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November 2013

FCB11N60

N-Channel SuperFET $^{\circledR}$ MOSFET 600 V, 11 A, 380 m Ω

Features

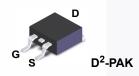
- 650V @ T_J = 150°C
- Typ. $R_{DS(on)}$ = 320 m Ω
- Ultra Low Gate Charge (Typ. Q_g = 40 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 95 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

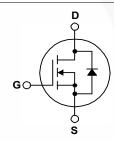
Application

- Lighting
- · Solar Inverter
- · AC-DC Power Supply

Description

SuperFET® MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low onresistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter	FCB11N60TM	Unit
V_{DSS}	Drain to Source Voltage		600	V
	Drain Current	- Continuous (T _C = 25°C)	11	Α
I _D	Diain Current	- Continuous (T _C = 100°C)	7	_ ^
I _{DM}	Drain Current	- Pulsed (Note 1)	33	Α
V _{GSS}	Gate to Source Voltage	±30	V	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		340	mJ
I _{AR}	Avalanche Current	Avalanche Current (Note 1)		Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		12.5	mJ
dv/dt	Peak Diode Recovery dv/	dt (Note 3)	4.5	V/ns
D	Dower Dissipation	$(T_C = 25^{\circ}C)$	125	W
P_{D}	Power Dissipation	- Derate Above 25°C	1.0	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	οС
TL	Maximum Lead Temperat	ure for Soldering, 1/8" from Case for 5 Seconds	300	°C

Thermal Characteristics

Symbol	Parameter	FCB11N60TM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.0	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (1 in ² Pad of 2-oz Copper), Max. 40		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCB11N60TM	FCB11N60	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
D	Drain to Course Broakdown Voltage	$V_{GS} = 0 \text{ V,I}_{D} = 250 \mu\text{A}, \text{ T}_{C} = 25^{\circ}\text{C}$	600	-	-	V
BV _{DSS} Drain to Source Breakdown Voltage		$V_{GS} = 0 \text{ V,I}_{D} = 250 \mu\text{A}, \text{ T}_{C} = 150^{\circ}\text{C}$	-	650	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	-	0.6	-	V/°C
BV _{DS}	Drain-Source Avalanche Breakdown Voltage	V _{GS} = 0 V, I _D = 11 A	-	700	-	V
	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V	-	-	1	
IDSS	Zero Gate voltage Drain Current	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	10	μΑ
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V_{GS} = 10 V, I_{D} = 5.5 A	-	0.32	0.38	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 40 \text{ V}, I_{D} = 5.5 \text{ A}$	-	9.7	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 05.V.V 0.V	- \	1148	1490	pF
C _{oss}	Output Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz		671	870	pF
C _{rss}	Reverse Transfer Capacitance			63	-	pF
C _{oss}	Output Capacitance	V _{DS} = 480 V, V _{GS} = 0 V, f = 1 MHz	-	35	-	pF
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V	-	95	-	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	34	80	ns
t _r	Turn-On Rise Time	$V_{DD} = 300 \text{ V}, I_{D} = 11 \text{ A},$ $V_{GS} = 10 \text{ V}, R_{G} = 25 \Omega$		98	205	ns
t _{d(off)}	Turn-Off Delay Time			119	250	ns
t _f	Turn-Off Fall Time	(Note 4) -	56	120	ns
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 480 V, I _D = 11 A,	-	40	52	nC
Q _{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	7.2	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4	-	21	_	nC

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current			-	11	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	33	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 11 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 11 A,	-	390	// -	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	5.7	-	μC

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. I_{AS} = 5.51 A, V_{DD} = 50 V, R_{G} = 25 Ω, starting T_{J} = 25°C. 3. I_{SD} ≤ 11 A, di/dt ≤ 200 A/μs, V_{DD} ≤ BV_{DSS}, starting T_{J} = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

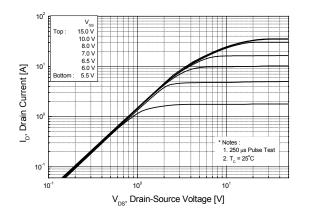


Figure 2. Transfer Characteristics

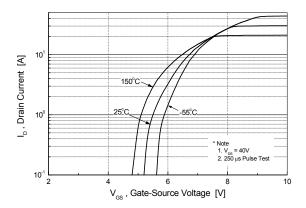


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

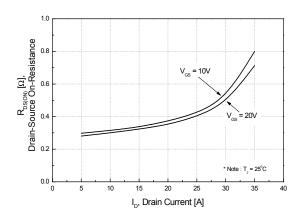


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

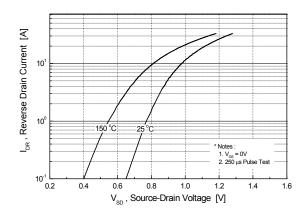


Figure 5. Capacitance Characteristics

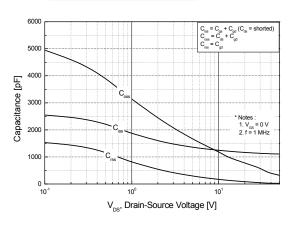
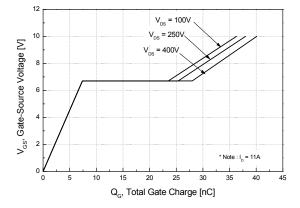


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

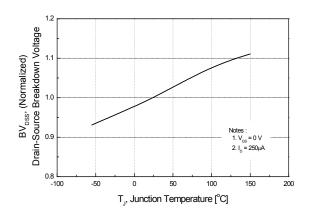


Figure 8. On-Resistance Variation vs. Temperature

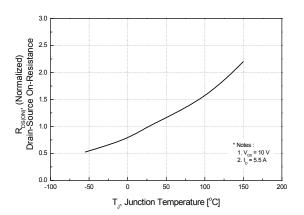


Figure 9. Maximum Safe Operating Area

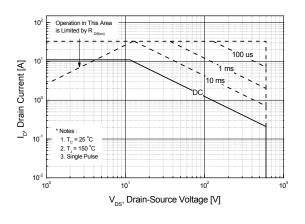


Figure 10. Maximum Drain Current vs. Case Temperature

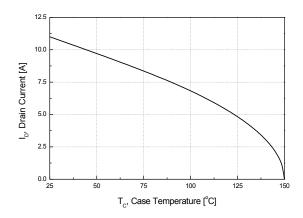
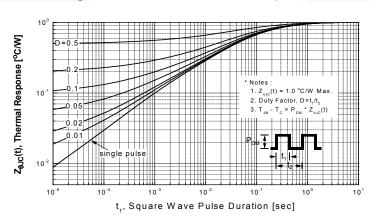


Figure 11. Transient Thermal Response Curve



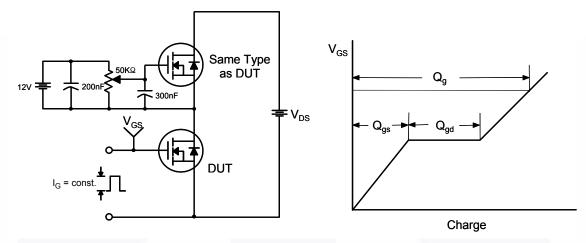


Figure 12. Gate Charge Test Circuit & Waveform

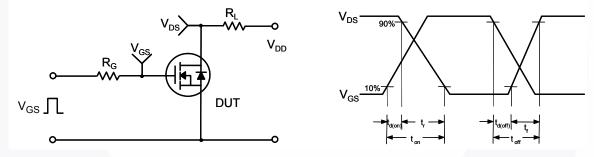


Figure 13. Resistive Switching Test Circuit & Waveforms

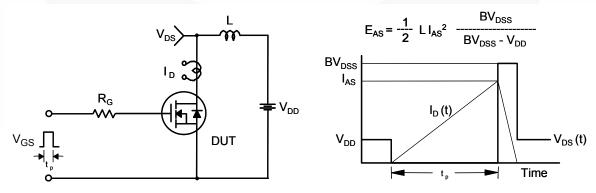


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

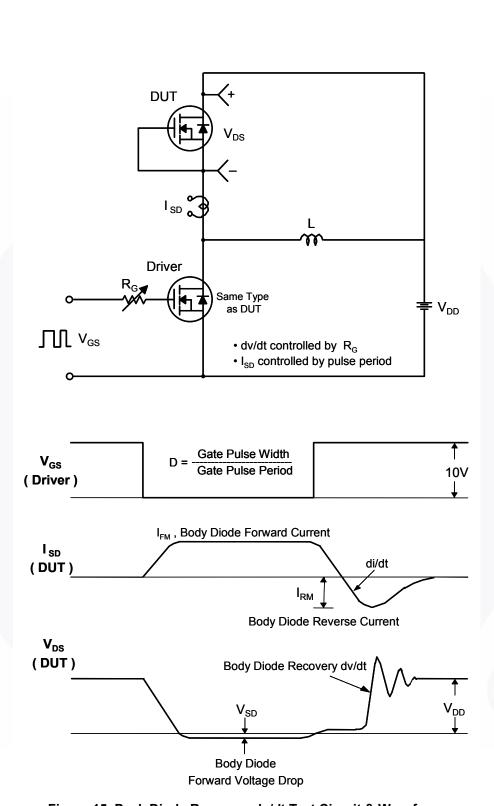


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

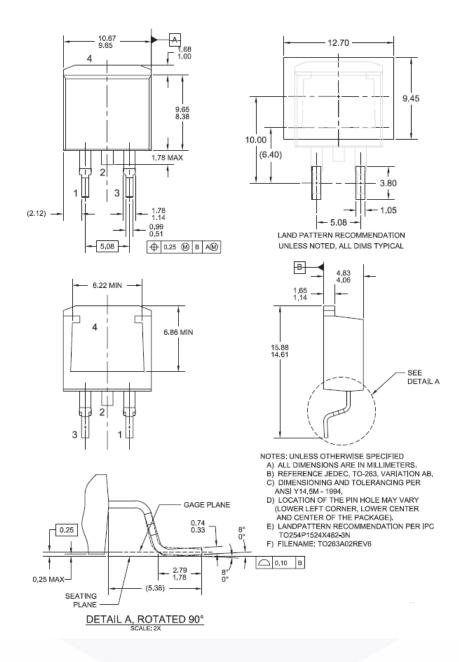


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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